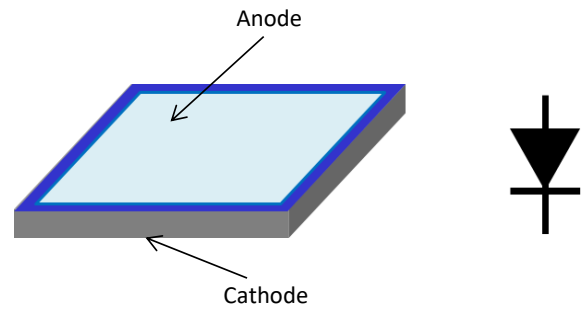


YJ Planar Schottky Barrier Diode Die Specification

30V 0.5A, 25mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB025L030AS-180A

Main Products Characteristics

- Average forward current: $I_{F(AV)} = 0.5 \text{ A}$
- Maximum operating junction temperature: $T_j = 125 \text{ }^\circ\text{C}$
- Top metal: AL



Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	30 V
Average forward current	$I_{F(AV)}$	0.5 A
Non-repetitive peak surge current ($t_p = 8.3 \text{ ms}$, halfwave, 1 cycle)	I_{FSM}	10 A
Storage temperature range	T_{stg}	-50 to +125 $^\circ\text{C}$
Maximum operating junction temperature	T_j	125 $^\circ\text{C}$

Static Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage $I_R = 1 \text{ mA}$	V_{BR}	34 V	39V
Maximum forward voltage drop $I_F = 0.5 \text{ A}$ Pulse Test: $t_p = 300 \mu\text{s}$, $\delta \leq 2\%$	V_F	0.55V	0.41V
Maximum reverse current $V_R = 30 \text{ V}$ Pulse Test: $t_p = 300 \mu\text{s}$, $\delta \leq 2\%$	I_R	200uA	15uA

Device Schematics and Outline Drawing

Die Thickness *	7Mils (180um)
Die Size **	25 Mils (630um)
Top Metal Pad	22Mils (560um)
Active Area	18.8 Mils (478um)
Top Metal	AL
Back Metal	Ag

Note: 1 * : Also can offer device with 8 mils thickness
2 ** : Cutting street width is around 70um

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangjie Electronics does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.